

61048

SILICON PHOTOTRANSISTOR
(TYPE GS4123)



Features:

- Hermetically sealed
- High Sensitivity
- Base lead provided for conventional transistor biasing
- Wide receiving angle for easy alignment
- Spectrally Matched to the 62030 Series LED.

Applications:

- Incremental Encoding
- Reflective Sensors
- Position Sensors
- Level Sensors

DESCRIPTION

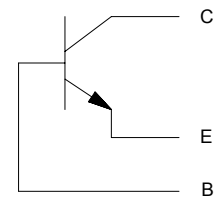
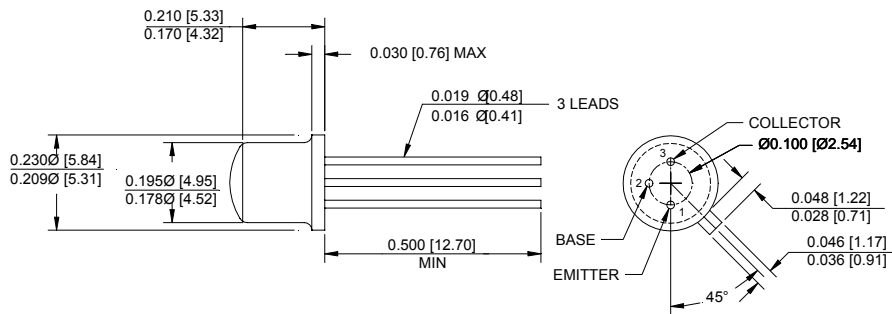
This is a N-P-N Planar Silicon phototransistor in a flat window TO-46 three-lead package featuring a large (0.06" X 0.06") sensitive area. It is available in a range of sensitivities and is ideal for use wherever system considerations dictate the use of external optics to focus radiation on the sensor. Available custom binned to customer specifications and/or screened to MIL-PRF-19500.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature.....	-65°C to +150°C
Operating Temperature (See part selection guide for actual operating temperature).....	-65°C to +125°C
Collector-Emitter Voltage.....	50V
Emitter-Collector Voltage.....	7V
Continuous Collector Current.....	50mA
Power Dissipation (Derate at the rate of 2.5 mW/°C above 25°C).....	250mW
Lead Soldering Temperature (1/16" from case for 10 seconds).....	240°C

Package Dimensions

Schematic Diagram



ALL DIMENSIONS ARE IN INCHES [MILLIMETERS]

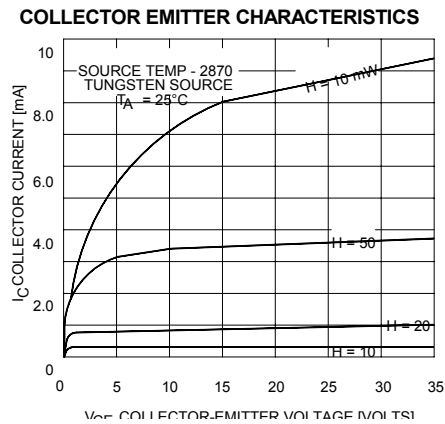
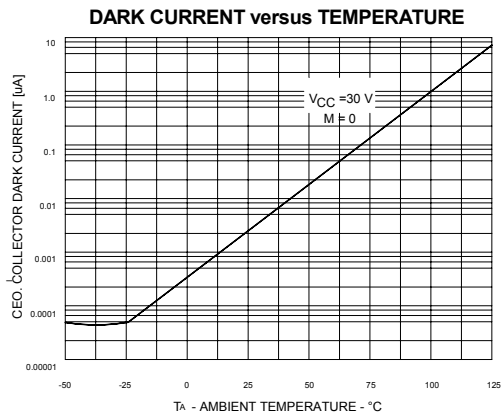
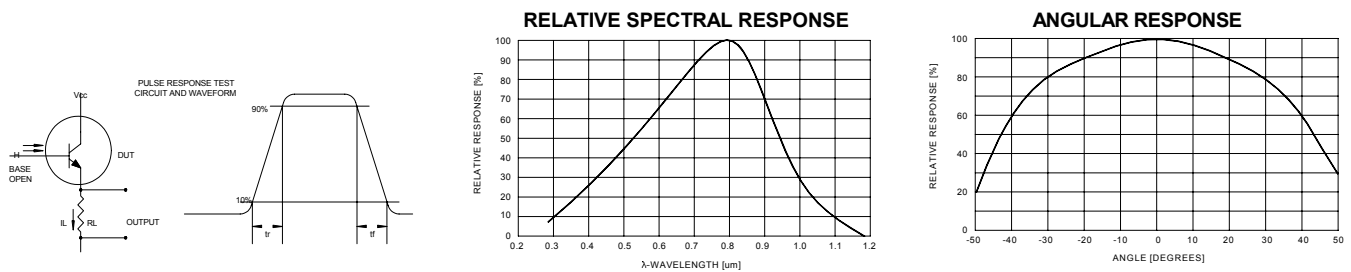
THE COLLECTOR IS IN ELECTRICAL CONTACT WITH THE CASE

ELECTRICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$ unless otherwise specified.

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
Light Current	I_L	5 20 30 50		20 30 50 --	mA	$V_{CE} = 5.0\text{V}$, $H = 20 \text{ mW/cm}^2$	1
Dark Current	I_D			50	nA	$V_{CE} = 5\text{V}$, $H = 0$	
Collector-Emitter Breakdown Voltage	BV_{CEO}	30			V	$I_C = 100\mu\text{A}$	
Emitter-Collector Breakdown Voltage	BV_{ECO}	7			V	$I_E = 100\mu\text{A}$	
Light Current Rise Time	t_r		8 10 15 20		μs	$R_L = 100\Omega$, $V_{CC} = 5\text{V}$, $I_L = 1.0\text{mA}$	
Saturation Voltage	$V_{CE}(\text{sat})$		0.2		V	$I_C = 0.4\text{mA}$, $H = 20 \text{ mW/cm}^2$	
Angular Response	θ		10		degrees		2

NOTES:

1. Irradiance in mW/cm^2 from tungsten source at a color temperature of 2870K.
2. The angle between incidence for peak response and incidence for 50% of peak response.



RECOMMENDED OPERATING CONDITIONS:

PARAMETER	SYMBOL	MIN	MAX	UNITS
Bias Voltage-Collector/Emitter	I_F	5	10	mA
Irradiance (H)	H	15	25	mW/cm^2

SELECTION GUIDE

PART NUMBER	PART DESCRIPTION	I_L Range
61048-001	Silicon Phototransistor in TO-46 package, commercial version	5 to 20mA
61048-101	Silicon Phototransistor in TO-46 package (-55° to +100°C) with 100% screening	5 to 20mA
61048-002	Silicon Phototransistor in TO-46 package, commercial version	20 to 30mA
61048-102	Silicon Phototransistor in TO-46 package (-55° to +100°C) with 100% screening	20 to 30mA
61048-003	Silicon Phototransistor in TO-46 package, commercial version	30 to 50mA
61048-103	Silicon Phototransistor in TO-46 package (-55° to +100°C) with 100% screening	30 to 50mA
61048-004	Silicon Phototransistor in TO-46 package, commercial version	+50mA
61048-104	Silicon Phototransistor in TO-46 package (-55° to +100°C) with 100% screening	+50mA